IS31AP4996

1.1W AUDIO POWER AMPLIFIER WITH ACTIVE-HIGH STANDBY MODE

May 2013

GENERAL DESCRIPTION

The IS31AP4996 has been designed for demanding audio applications such as mobile phones and permits the reduction of the number of external components.

It is capable of delivering 1.1W of continuous RMS output power into an 8Ω load @ 5V.

An externally-controlled standby mode reduces the supply current to much less than 2μA. It also includes internal thermal shutdown protection.

The unity-gain stable amplifier can be configured by external gain setting resistors.

FEATURES

- Operating from V_{CC} = 2.7V ~ 5.5V
- 1.1W output power @ V_{CC} = 5V, THD+N= 1%, f = 1kHz, with 8Ω load
- Ultra-low consumption in standby mode (much less than 2μA)
- 56dB PSRR @217Hz in grounded mode
- Near-zero click-and-pop
- Ultra-low distortion (0.074%@0.5W, 1kHz)
- SOP-8 and MSOP-8 package

APPLICATIONS

- Mobile phones
- PDAs
- Portable electronic devices
- Notebook computer

TYPICAL APPLICATION CIRCUIT

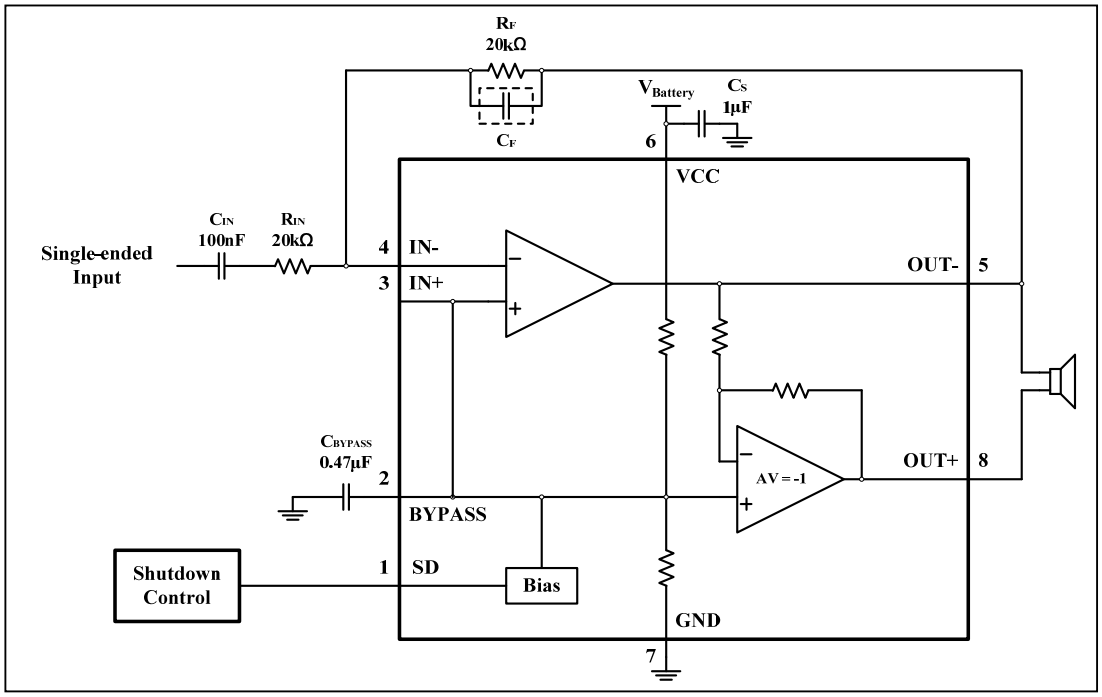
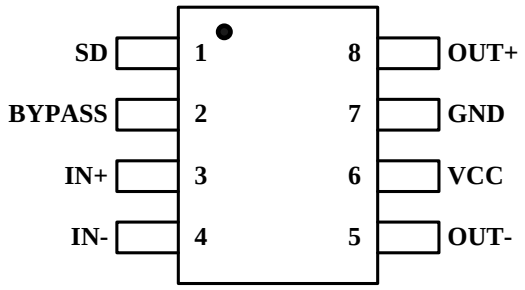


Figure 1 Typical Application Circuit

PIN CONFIGURATION

Package	Pin Configuration (Top View)
SOP-8 MSOP-8	

PIN DESCRIPTION

No.	Pin	Description
1	SD	The device enters shutdown mode when a high level is applied on this pin.
2	BYPASS	Bypass capacitor pin which provides the common mode voltage (V_{CC}/2).
3	IN+	Positive input of the first amplifier.
4	IN-	Negative input of the first amplifier, receives the audio input signal. Connected to the feedback resistor R_F and to the input resistor R_{IN}.
5	OUT-	Negative output of the IS31AP4996. Connected to the load and to the feedback resistor R_F.
6	VCC	Positive analog supply of the chip.
7	GND	Ground.
8	OUT+	Positive output of the IS31AP4996. Connected to the load.

ORDERING INFORMATION

Industrial Range: -40°C to +85°C

Order Part No.	Package	QTY/Reel
IS31AP4996-GRLS2-TR	SOP-8, Lead-free	2500
IS31AP4996-SLS2-TR	MSOP-8, Lead-free	2500

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a.) the risk of injury or damage has been minimized;
b.) the user assume all such risks; and
c.) potential liability of Integrated Silicon Solution, Inc is adequately protected under the circumstances

ABSOLUTE MAXIMUM RATINGS (Note 1)

Supply voltage, V_{CC}	−0.3V ~ +6.0V
Voltage at any input pin	−0.3V ~ V_{CC}+0.3V
Maximum junction temperature, T_{JMAX}	150°C
Storage temperature range, T_{STG}	−65°C ~ +150°C
Operating temperature range, T_A	−40°C ~ +85°C
Maximum power dissipation, SOP-8(25°C/85°C) (Note 2) MSOP-8(25°C/85°C)	720mW/380mW 590mW/310mW

Note 1: Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only and functional operation of the device at these or any other condition beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.
Note 2: Thermal simulation @ 25°C /85°C ambient temperature, still air convection, 2s2p boards according to JESD51. The Pd (max by package) is evaluated by (Tjmax-Ta)/Theta-Ja.

ELECTRICAL CHARACTERISTICS

The following specifications apply for C_{IN} = 0.1µF, R_{IN} = R_F = 20kΩ, C_{BYPASS} = 0.47µF, unless otherwise specified. Limits apply for T_A = 25°C. V_{CC}=5V (Note 3 or specified)

Symbol	Parameter	Condition		Min.	Typ.	Max.	Unit
I_{CC}	Quiescent power supply current	Io = 0A, no Load			3.0		mA
I_{SD}	Standby current	V_{SD} = V_{CC}, R_L = ∞				2	µA
V_{SD_H}	Shutdown voltage input high	V_{CC} = 5.5V		1.4			V
V_{SD_L}	Shutdown voltage input low	V_{CC} = 2.7V				0.4	V
V_{OS}	Output offset voltage					15	mV
Po	Output power (8Ω)	THD+N = 1%; f = 1kHz			1.15		W
		THD+N = 10%; f = 1kHz			1.40		
t_{WU}	Wake-up time *(Note 4)*	C_{BYPASS} = 0.47µF			100	250	ms
THD+N	Total harmonic distortion+noise *(Note 4)*	Po = 0.5Wrms; f = 1kHz			0.074		%
PSRR	Power supply rejection ratio *(Note 4)*	Vripple p-p = 200mV Input Grounded	f = 217Hz		56		dB
			f = 1kHz		68		

The following specifications apply for C_{IN} = 0.1µF, R_{IN} = R_F = 20kΩ, C_{BYPASS} = 0.47µF, unless otherwise specified. Limits apply for T_A = 25°C. V_{CC}=3V (Note 3 or specified)

Symbol	Parameter	Condition	Min.	Typ.	Max.	Unit
I_{CC}	Quiescent power supply current	Io = 0A, no Load		2.2		mA
I_{SD}	Standby current	V_{SD} = V_{CC}, R_L = ∞			2	µA
Po	Output power (8Ω)	THD+N = 1%; f = 1kHz		380		mW
		THD+N = 10%; f = 1kHz		490		
t_{WU}	Wake-up time *(Note 4)*	C_{BYPASS} = 0.47µF		90	200	ms
THD+N	Total harmonic distortion+noise *(Note 4)*	Po = 0.3Wrms; f = 1kHz		0.076		%

Note 3: Production testing of the device is performed at 25°C. Functional operation of the device and parameters specified over other temperature range, are guaranteed by design, characterization and process control.
Note 4: Guaranteed by design.

TYPICAL PERFORMANCE CHARACTERISTIC

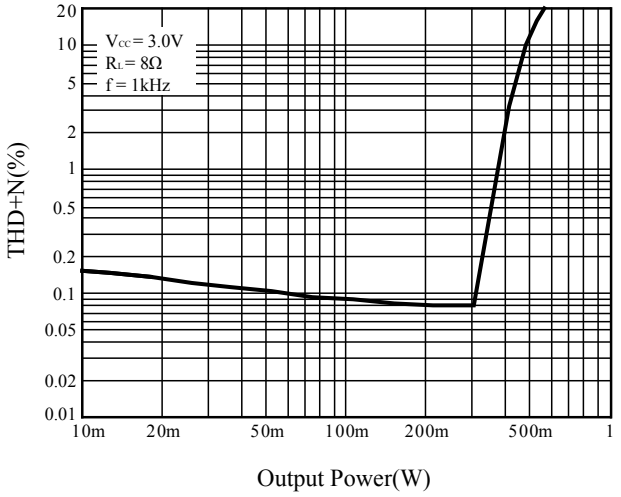


Figure 2 THD+N vs. Output Power

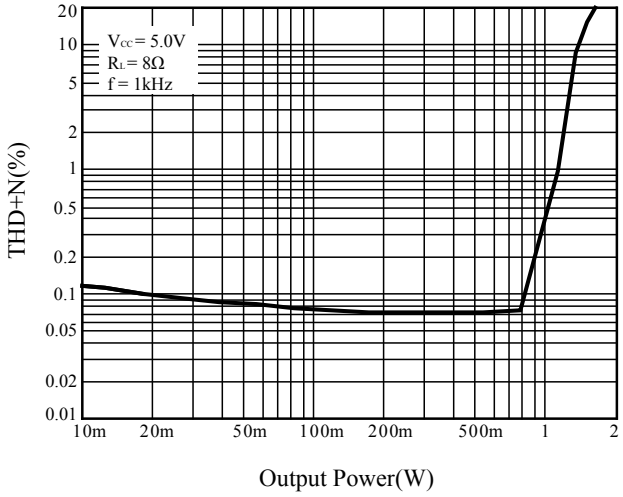


Figure 3 THD+N vs. Output Power

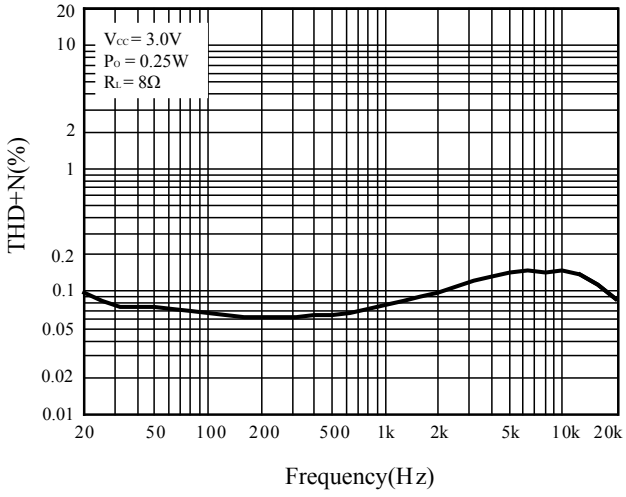


Figure 4 THD+N vs. Frequency

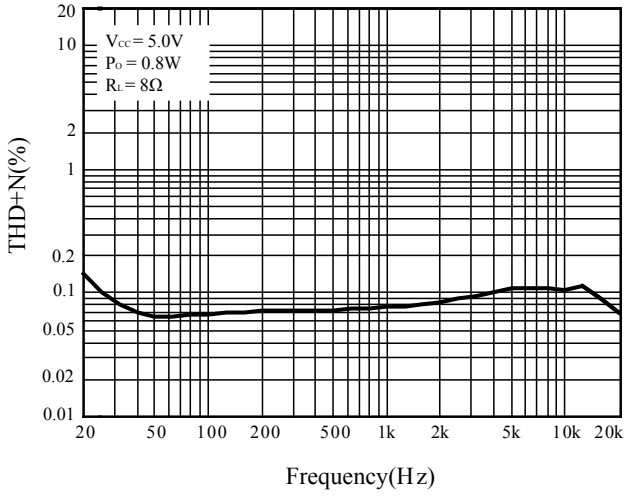


Figure 5 THD+N vs. Frequency

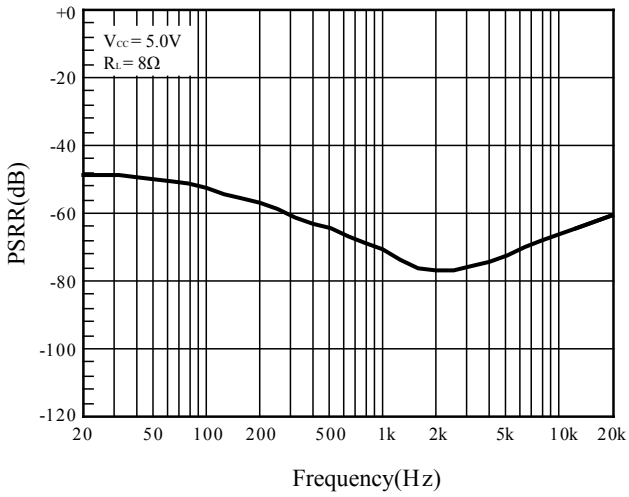


Figure 6 PSRR vs. Frequency

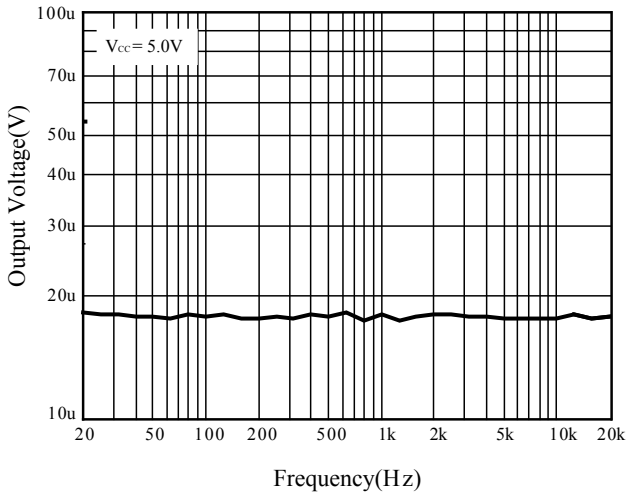


Figure 7 Noise Floor

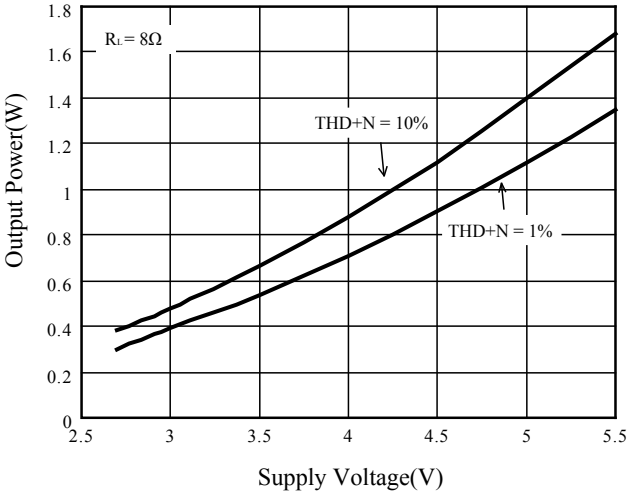


Figure 8 Output Power vs. Power Supply

APPLICATION INFORMATION

BTL CONFIGURATION PRINCIPLE

The IS31AP4996 is a monolithic power amplifier with a BTL output type. BTL (bridge tied load) means that each end of the load is connected to two single-ended output amplifiers. Thus, we have:

Single-ended output 1 = V_{OUT+} = V_{OUT} (V)

Single ended output 2 = V_{OUT-} = -V_{OUT} (V)

and

V_{OUT}+ - V_{OUT-} = 2V_{OUT} (V)

The output power is:

$$P_{OUT} = \frac{(2V_{OUT\ RMS})^2}{R_L}$$

For the same power supply voltage, the output power in BTL configuration is four times higher than the output power in single ended configuration.

GAIN IN A TYPICAL APPLICATION SCHEMATIC

The typical application schematic is shown in Figure 1.

In the flat region (no C_{IN} effect), the output voltage of the first stage is (in Volts):

$$V_{OUT-} = (-V_{IN})\frac{R_F}{R_{IN}}$$

For the second stage: V_{OUT+} = -V_{OUT-} (V)

The differential output voltage is (in Volts):

$$V_{OUT+} - V_{OUT-} = 2V_{IN}\frac{R_F}{R_{IN}}$$

The differential gain, G_V, is given by:

$$G_v = \frac{V_{OUT+} - V_{OUT-}}{V_{IN}} = 2\frac{R_F}{R_{IN}}$$

V_{OUT-} is in phase with V_{IN} and V_{OUT+} is phased 180° with V_{IN}. This means that the positive terminal of the loudspeaker should be connected to V_{OUT+} and the negative to V_{OUT-}.

LOW AND HIGH FREQUENCY RESPONSE

In the low frequency region, C_{IN} starts to have an effect. C_{IN} forms with R_{IN} a high-pass filter with a -3dB cut-off frequency. f_{CL} is in Hz.

$$f_{CL} = \frac{1}{2\pi R_{IN} C_{IN}}$$

In the high frequency region, you can limit the bandwidth by adding a capacitor (C_F) in parallel with R_F. It forms a low-pass filter with a -3dB cut-off frequency. f_{CH} is in Hz.

$$f_{CH} = \frac{1}{2\pi R_F C_F}$$

DECOUPLING OF THE CIRCUIT

Two capacitors are needed to correctly bypass the IS31AP4996: a power supply bypass capacitor C_S and a bias voltage bypass capacitor C_{BYPASS}.

C_S has particular influence on the THD+N in the high frequency region (above 7kHz) and an indirect influence on power supply disturbances. With a value for C_S of 1µF, you can expect THD+N levels similar to those shown in the datasheet.

In the high frequency region, if C_S is lower than 1µF, it increases THD+N and disturbances on the power supply rail are less filtered.

On the other hand, if C_S is higher than 1µF, those disturbances on the power supply rail are more filtered.

C_{BYPASS} has an influence on THD+N at lower frequencies, but its function is critical to the final result of PSRR (with input grounded and in the lower frequency region).

If C_{BYPASS} is lower than 0.47µF, THD+N increases at lower frequencies and PSRR worsens.

If C_{BYPASS} is higher than 0.47µF, the benefit on THD+N at lower frequencies is small, but the benefit to PSRR is substantial.

Note that C_{IN} has a non-negligible effect on PSRR at lower frequencies. The lower the value of C_{IN}, the higher the PSRR is.

WAKE-UP TIME (t_{WU})

When the standby is released to put the device on, the bypass capacitor C_{BYPASS} will not be charged immediately. As C_{BYPASS} is directly linked to the bias of the amplifier, the bias will not work properly until the C_{BYPASS} voltage is correct. The time to reach this voltage is called wake-up time or t_{WU} and specified in the electrical characteristics table with C_{BYPASS} = 0.47µF.

POP PERFORMANCE

Pop performance is intimately linked with the size of the input capacitor C_{IN} and the bias voltage bypass capacitor C_{BYPASS}.

The size of C_{IN} is dependent on the lower cut-off frequency and PSRR values requested. The size of C_{BYPASS} is dependent on THD+N and PSRR values requested at lower frequencies.

Moreover, C_{BYPASS} determines the speed with which the amplifier turns on.

CLASSIFICATION REFLOW PROFILES

Profile Feature	Pb-Free Assembly
Preheat & Soak Temperature min (Tsmin) Temperature max (Tsmax) Time (Tsmin to Tsmax) (ts)	150°C 200°C 60-120 seconds
Average ramp-up rate (Tsmax to Tp)	3°C/second max.
Liquidous temperature (TL) Time at liquidous (tL)	217°C 60-150 seconds
Peak package body temperature (Tp)*	Max 260°C
Time (tp)** within 5°C of the specified classification temperature (Tc)	Max 30 seconds
Average ramp-down rate (Tp to Tsmax)	6°C/second max.
Time 25°C to peak temperature	8 minutes max.

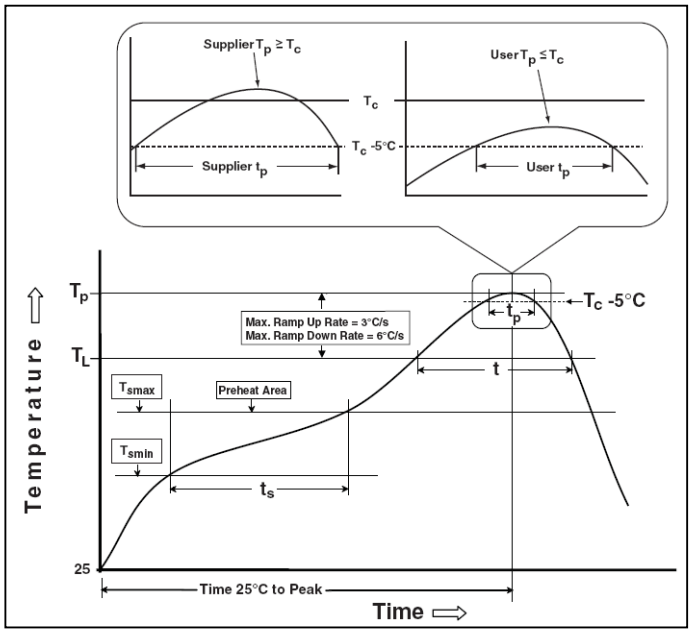
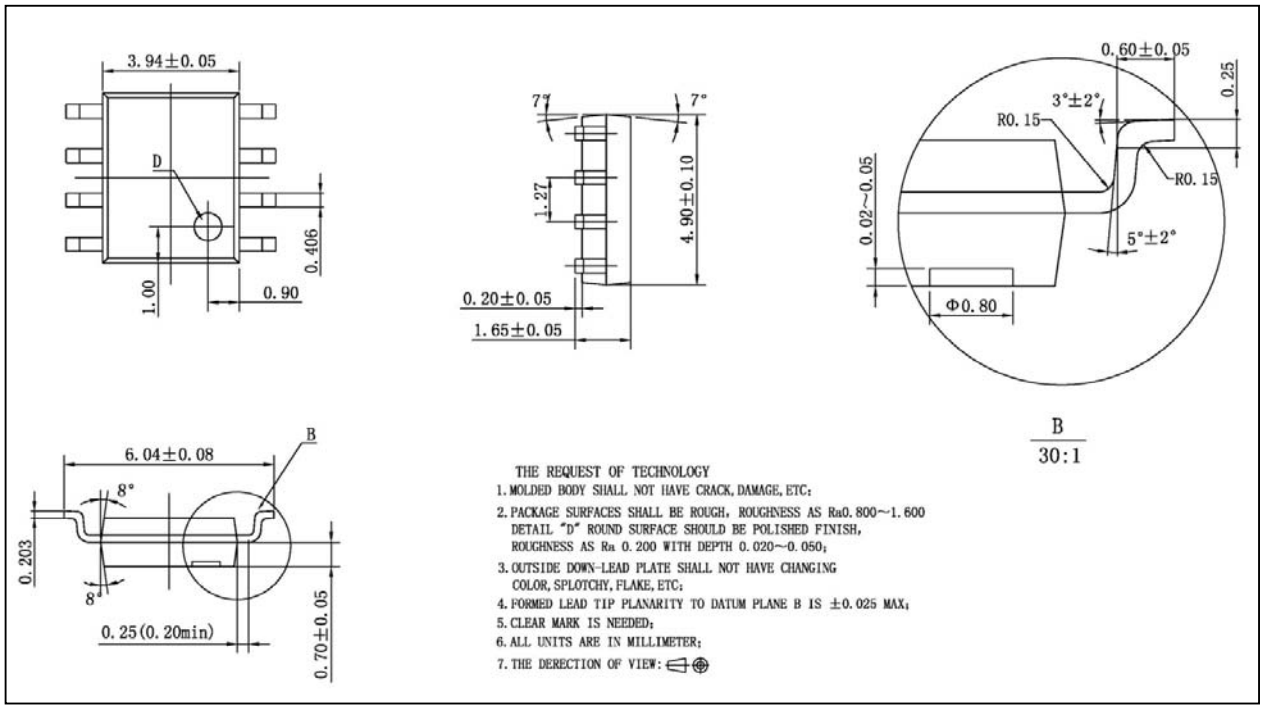


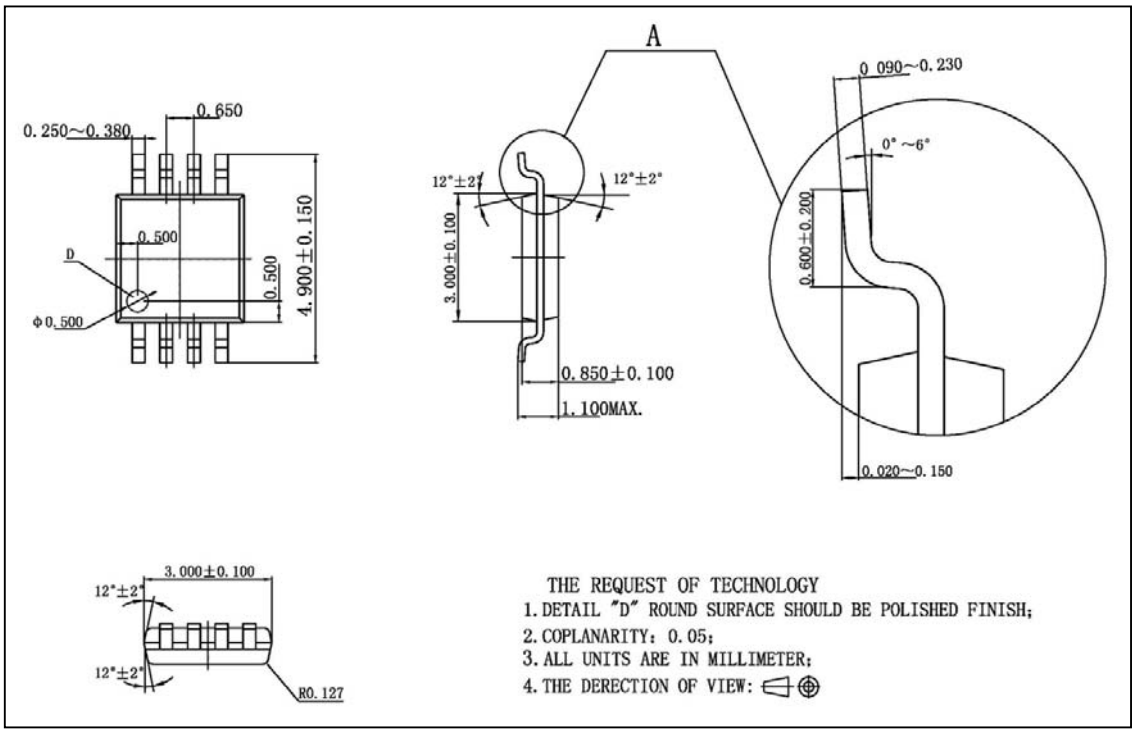
Figure 9 Classification Profile

PACKAGE INFORMATION

SOP-8



MSOP-8


A
0.650
0.250~0.380
0.500
D
0.500
4.900±0.150
φ0.500
12°±2°
12°±2°
3.000±0.100
0.850±0.100
1.100MAX.
0.090~0.230
0°~6°
0.600±0.200
0.020~0.150
3.000±0.100
12°±2°
12°±2°
R0.127
THE REQUEST OF TECHNOLOGY
1. DETAIL "D" ROUND SURFACE SHOULD BE POLISHED FINISH;
2. COPLANARITY: 0.05;
3. ALL UNITS ARE IN MILLIMETER;
4. THE DERECTION OF VIEW: